

# **BUK765R2-40B**

# N-channel TrenchMOS standard level FET Rev. 3 — 22 November 2011

Product data sheet

#### 1. **Product profile**

## 1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

## 1.2 Features and benefits

- Q101 compliant
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

## 1.3 Applications

- 12 V loads
- Automotive systems

- General purpose power switching
- Motors, lamps and solenoids

## 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	40	V
I <sub>D</sub>	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{See } \frac{\text{Figure 3}}{\text{Figure 3}}};$	-	-	75	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	203	W
Static chara	cteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 11</u> ; see <u>Figure 12</u>	-	4.4	5.2	mΩ
Dynamic ch	aracteristics					
$Q_{GD}$	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; V_{DS} = 32 \text{ V};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{\text{ Composition}}$	-	16	-	nC
Avalanche r	uggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 75 A; $V_{sup} \le 40$ V; $R_{GS}$ = 50 $\Omega$ ; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped	-	-	494	mJ

<sup>[1]</sup> Continuous current is limited by package.



# 2. Pinning information

Table 2. Pinning information

I GIOTO E.		mormation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain[1]	mb	D
3	S	source		
mb	D mounting base; connected to drain		mbb076 S	
			SOT404 (D2PAK)	

<sup>[1]</sup> It is not possible to make a connection to pin 2.

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK765R2-40B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	40	V
$V_{DGR}$	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	40	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{see } \frac{\text{Figure 1}}{\text{Figure 1}};$	<u>[1]</u>	-	143	Α
		see <u>Figure 3</u>	[2]	-	75	Α
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 10 V; see <u>Figure 1</u>	[2]	-	75	Α
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \mu s$ ; see Figure 3		-	573	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	203	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-dra	ain diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	143	Α
			[2]	-	75	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	573	Α
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 75 A; $V_{sup} \le 40$ V; $R_{GS}$ = 50 $\Omega$ ; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	494	mJ

- [1] Current is limited by power dissipation chip rating.
- [2] Continuous current is limited by package.

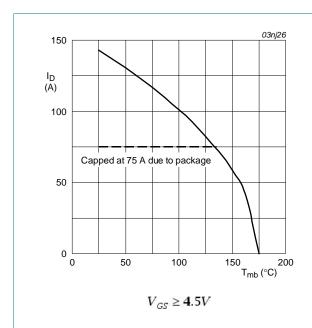


Fig 1. Continuous drain current as a function of mounting base temperature

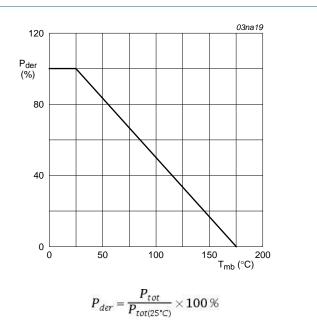


Fig 2. Normalized total power dissipation as a function of mounting base temperature

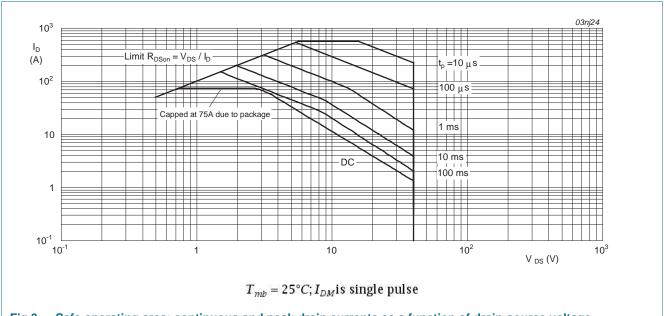


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

## 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.74	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	minimum footprint; mounted on a printed-circuit board	-	50	-	K/W

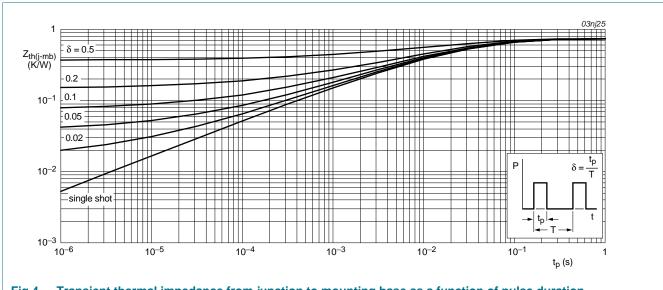


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub> drain-source breakdown		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	40	-	-	V
	voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	36	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see <u>Figure 10</u>	2	3	4	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = -55$ °C; see Figure 10	-	-	4.4	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 175$ °C; see Figure 10	1	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μΑ
		$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
D0011	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 175 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	-	9.9	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 11; see Figure 12	-	4.4	5.2	mΩ
Dynamic ch	naracteristics					
$Q_{G(tot)}$	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$	-	52	-	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C; see <u>Figure 13</u>	-	12	-	nC
$Q_{GD}$	gate-drain charge		-	16	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 14}{\text{ V}}$	-	2842	3789	pF
C <sub>oss</sub>	output capacitance		-	711	853	pF
$C_{rss}$	reverse transfer capacitance		-	296	406	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$	-	15	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 10 \Omega$ ; $T_j = 25 °C$	-	51	-	ns
$t_{d(off)}$	turn-off delay time		-	81	-	ns
t <sub>f</sub>	fall time		-	56	-	ns
L <sub>D</sub>	internal drain inductance	from drain lead 6 mm from package to centre of die ; $T_j = 25$ °C	-	4.5	-	nΗ
		from upper edge of drain mounting base to centre of die; $T_j = 25$ °C	-	2.5	-	nΗ
L <sub>S</sub>	internal source inductance	from source lead to source bond pad ; $T_j = 25  ^{\circ}\text{C}$	-	7.5	-	nΗ
Source-drai	in diode					
$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see <u>Figure 15</u>	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	54	-	ns
Qr	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 20 \text{ V}; T_j = 25 \text{ °C}$	-	38	-	nC

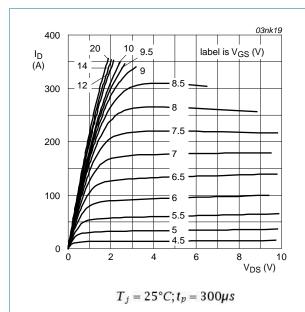


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

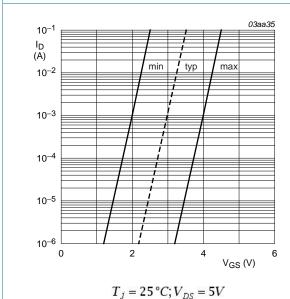
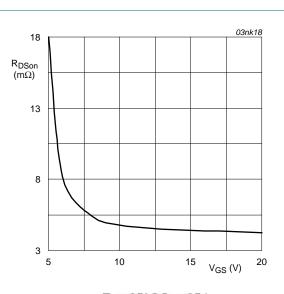
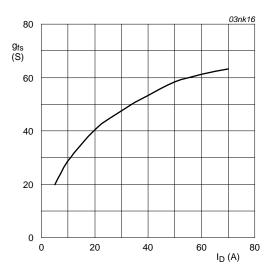


Fig 7. Sub-threshold drain current as a function of gate-source voltage



 $T_j = 25^{\circ}C; I_D = 25A$ 

Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values



 $T_j = 25^{\circ}C; V_{DS} = 25V$ 

Fig 8. Forward transconductance as a function of drain current; typical values

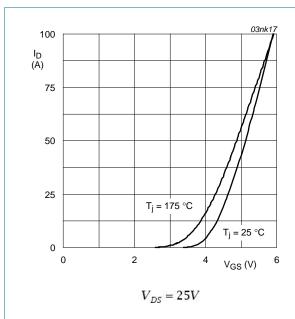


Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

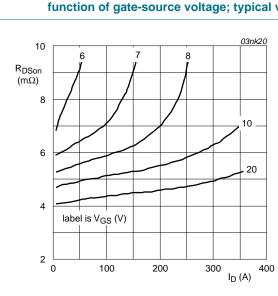
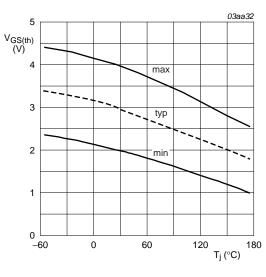


Fig 11. Drain-source on-state resistance as a function of drain current; typical values

 $T_j = 25^{\circ}C$ 



 $I_D = 1 mA; V_{DS} = V_{GS}$ 

Fig 10. Gate-source threshold voltage as a function of junction temperature

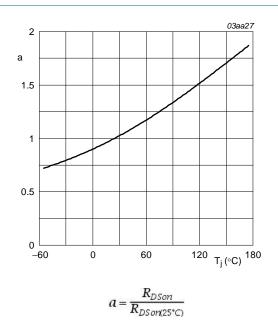


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

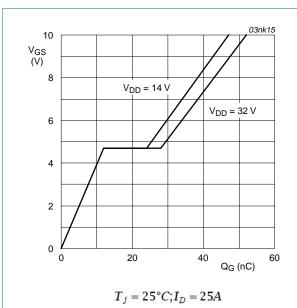
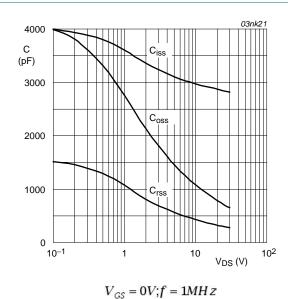


Fig 13. Gate-source voltage as a function of gate charge; typical values



G5 -- 11

Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

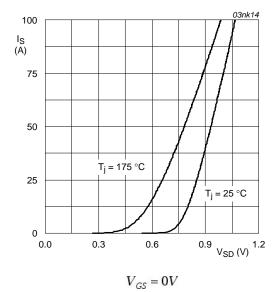


Fig 15. Source current as a function of source-drain voltage; typical values

## 7. Package outline

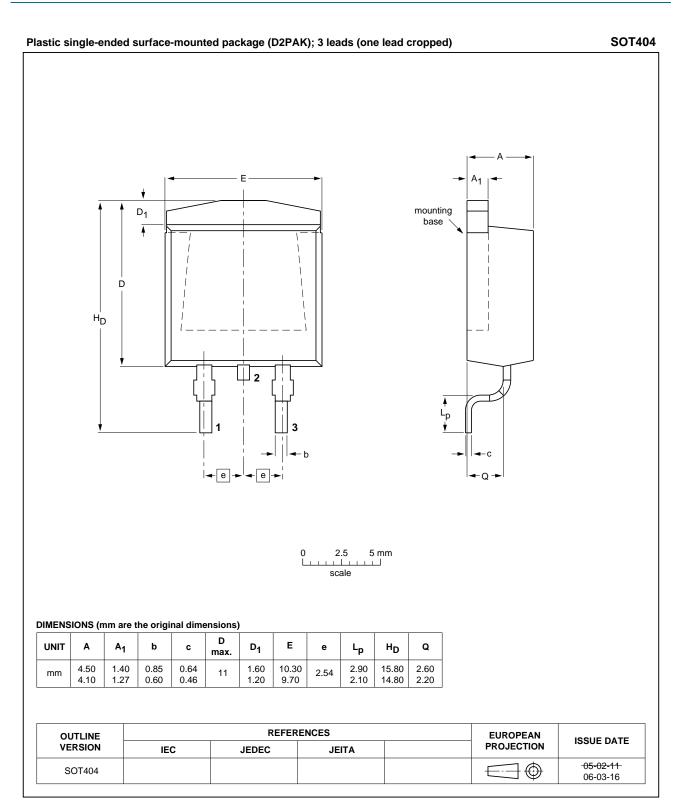


Fig 16. Package outline SOT404 (D2PAK)

# 8. Revision history

## Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK765R2-40B v.3	20111122	Product data sheet	-	BUK765R2-40B v.2
Modifications: • Various changes to content.				
BUK765R2-40B v.2	20090116	Product data sheet	-	BUK75_765R2_40B v.1

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#### 9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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